

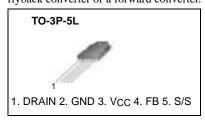
KA1M0965R Fairchild Power Switch(FPS)

Features

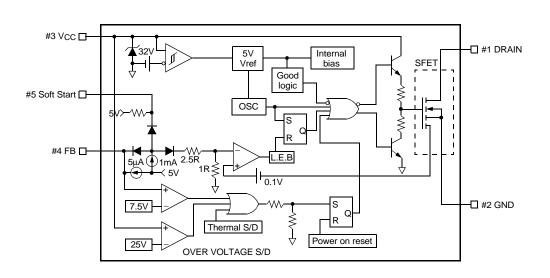
- Precision Fixed Operating Frequency (67kHz)
- Pulse by Pulse Over Current Limiting
- Over Load Protection
- Over Voltage Protection (Min. 23V)
- Internal Thermal Shutdown Function
- Under Voltage Lockout
- Internal High Voltage Sense FET
- Auto Restart
- Soft Start

Description

The Fairchild Power Switch(FPS) product family is specially designed for an off line SMPS with minimal external components. The Fairchild Power Switch(FPS) consist of high voltage power SenseFET and current mode PWM controller IC. PWM controller features integrated fixed oscillator, under voltage lock out, leading edge blanking, optimized gate turn-on/turn-off driver, thermal shut down protection, over voltage protection, temperature compensated precision current sources for loop compensation and fault protection circuit. compared to discrete MOSFET and controller or RCC switching converter solution, a Fairchild Power Switch(FPS) can reduce total component count, design size, weight and at the same time increase & efficiency, productivity, and system reliability. It has a basic platform well suited for cost effective design in either a flyback converter or a forward converter.



Internal Block Diagram



Absolute Maximum Ratings

Parameter	Symbol	Value	Unit	
Drain Gate Voltage (RGS=1MΩ)	Vdgr	650	V	
Gate-Source (GND) Voltage	Vgs	±30	V	
Drain Current Pulsed ⁽²⁾	IDM	36.0	ADC	
Single Pulsed Avalanche Energy (3)	Eas	950	mJ	
Continuous Drain Current (Tc=25°C)	ID	9.0	ADC	
Continuous Drain Current (T _C =100°C)	ID	5.8	ADC	
Maximum Supply Voltage	VCC,MAX	30	V	
Input Voltage Range	VFB	-0.3 to V _{SD}	V	
Total Dower Dissipation	PD	170	W	
Total Power Dissipation	Darting	1.33	W/°C	
Operating Ambient Temperature	TA	-25 to +85	°C	
Storage Temperature	TSTG	-55 to +150	°C	

Notes:

1. Tj = 25°C to 150°C

2. Repetitive rating: Pulse width limited by maximum junction temperature

3. L = 20mH, VDD = 50V, RG = 27 Ω , starting Tj = 25°C

Electrical Characteristics (SFET part)

(Ta=25°C unless otherwise specified)

Parameter	Symbol	Condition	Min.	Тур.	Max.	Unit
Drain-Source Breakdown Voltage	BVDSS	VGS=0V, ID=50µA	650	-	-	V
Zero Gate Voltage Drain Current	IDSS	VDS=Max., Rating, VGS=0V	-	-	50	μΑ
		V _{DS} =0.8Max., Rating, V _{GS} =0V, T _C =125°C	-	-	200	μΑ
Static Drain-Source on Resistance (Note)	RDS(ON)	V _{GS} =10V, I _D =4.5A	-	0.96	1.2	Ω
Forward Transconductance (Note)	gfs	V _{DS} =15V, I _D =4.5A	5.0	-	-	S
Input Capacitance	Ciss		-	1750	-	
Output Capacitance	Coss	VGS=0V, VDS=25V, f=1MHz	-	190	-	pF
Reverse Transfer Capacitance	Crss		-	78	-	
Turn on Delay Time	td(on)	VDD=0.5BVDSS, ID=9.0A	-	20	50	
Rise Time	tr	(MOSFET switching time are essentially	-	23	55	nS
Turn Off Delay Time	td(off)	independent of	-	85	180	115
Fall Time	tf	operating temperature)	-	30	70	
Total Gate Charge (Gate-Source+Gate-Drain)	Qg	V _{GS} =10V, I _D =9.0A, V _{DS} =0.5BV _{DSS} (MOSFET	-	74	75	
Gate-Source Charge	Qgs	switching time are essentially independent of	-	12	-	nC
Gate-Drain (Miller) Charge	Qgd	operating temperature)	-	35.4	-	

Note:

1. Pulse test: Pulse width $\leq 300 \mu S,$ duty cycle $\leq 2\%$

2. S = $\frac{1}{R}$

Electrical Characteristics (Control Part) (Continued)

(Ta=25°C unless otherwise specified)

Parameter	Symbol	Condition	Min.	Тур.	Max.	Unit	
UVLO SECTION							
Start Threshold Voltage	VSTART	-	14	15	16	V	
Stop Threshold Voltage	VSTOP	After turn on	9	10	11	V	
OSCILLATOR SECTION							
Initial Accuracy	Fosc	Ta=25°C	61	67	73	kHz	
Frequency Change With Temperature (2)	$\Delta F / \Delta T$	-25°C ≤ Ta ≤ +85°C	-	±5	±10	%	
Maximum Duty Cycle	Dmax	-	74	77	80	%	
FEEDBACK SECTION							
Feedback Source Current	IFB	Ta=25°C, $0V \le Vfb \le 3V$	0.7	0.9	1.1	mA	
Shutdown Feedback Voltage	Vsd	-	6.9	7.5	8.1	V	
Shutdown Delay Current	Idelay	Ta=25°C, $5V \le Vfb \le VSD$	4.0	5.0	6.0	μΑ	
SOFT START SECTION							
Soft Start Voltage	Vss	VFB =2V	4.7	5.0	5.3	V	
Soft Start Current	Iss	Sync & S/S=GND	0.8	1.0	1.2	mA	
REFERENCE SECTION							
Output Voltage ⁽¹⁾	Vref	Ta=25°C	4.80	5.00	5.20	V	
Temperature Stability ⁽¹⁾⁽²⁾	Vref/∆T	-25°C ≤ Ta ≤ +85°C	-	0.3	0.6	mV/°C	
CURRENT LIMIT (SELF-PROTECTION) SECTION							
Peak Current Limit	IOVER	Max. inductor current	5.28	6.00	6.72	Α	
PROTECTION SECTION						•	
Thermal Shutdown Temperature (Tj) ⁽¹⁾	TSD	-	140	160	-	°C	
Over Voltage Protection Voltage	Vovp	-	23	25	28	V	
TOTAL DEVICE SECTION							
Start-Up Current	ISTART	VCC=14V	0.1	0.3	0.4	mA	
Operating Supply Current (Control Part Only)	IOP	Ta=25°C	6	12	18	mA	
VCC Zener Voltage	Vz	ICC=20mA	30	32.5	35	V	

Notes:

1. These parameters, although guaranteed, are not 100% tested in production

2. These parameters, although guaranteed, are tested in EDS (wafer test) process

3. The amplitude of the sync. pulse is recommended to be between 2V and 3V for stable sync. function.

Typical Performance Characteristics

(These characteristic graphs are normalized at Ta=25°C)

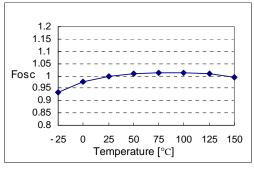


Figure 1. Operating Frequency

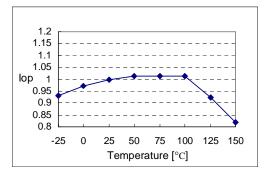


Figure 3. Operating Supply Current

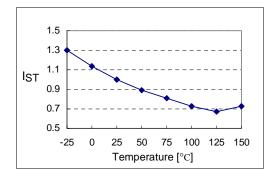


Figure 5. Start up Current

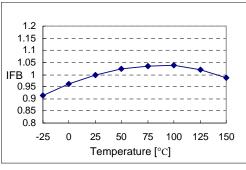


Figure 2. Feedback Source Current

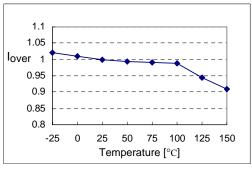


Figure 4. Peak Current Limit

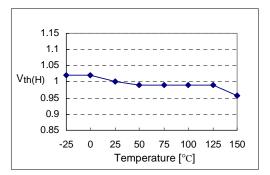


Figure 6. Start Threshold Voltage

Typical Performance Characteristics (Continued)

(These characteristic graphs are normalized at Ta=25°C)

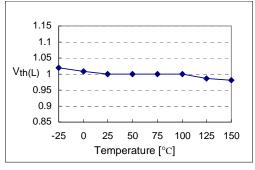


Figure 7. Stop Threshold Voltage

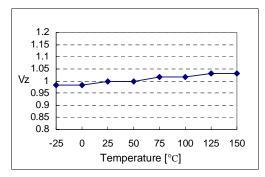


Figure 9. Vcc Zener Voltage

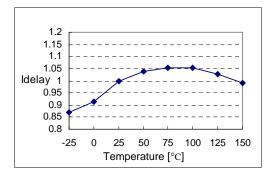


Figure 11. Shutdown Delay Current

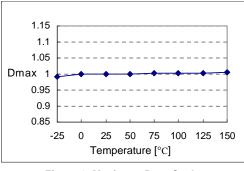


Figure 8. Maximum Duty Cycle

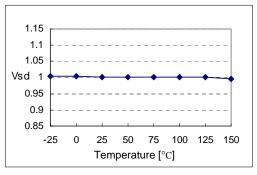


Figure 10. Shutdown Feedback Voltage

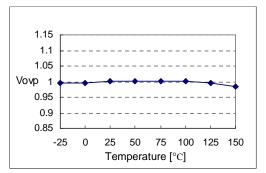


Figure 12. Over Voltage Protection

Typical Performance Characteristics (Continued)

(These characteristic groups are normalized at Ta=25°C)

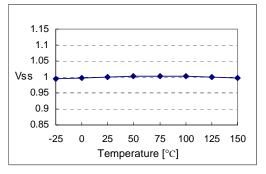


Figure 13. Soft Start Voltage

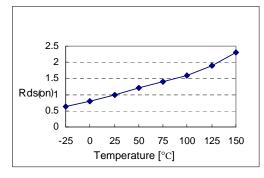
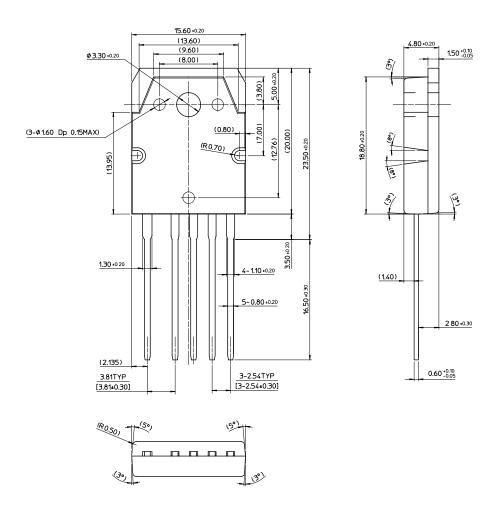
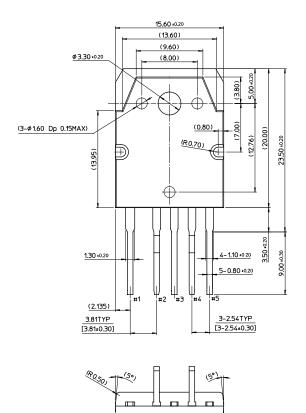


Figure 14. Static Drain Source on Resistance

Package Dimensions

TO-3P-5L

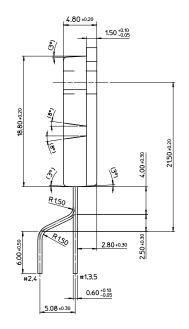




3)

(30)

TO-3P-5L (Forming)



Ordering Information

Product Number	Package	Rating	Operating Temperature
KA1M0965RTU	TO-3P-5L	650V. 9A	-25°C to +85°C
KA1M0965RYDTU	TO-3P-5L(Forming)	050V, 9A	-25 C 10 +65 C

TU : Non Forming Type

YDTU : Forming Type

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- A critical component in any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

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